

Description

The STP9527 uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 2.5V. This

device is suitable for use as a

Battery protection or in other Switching application.



General Features SOP-8

 $V_{DS} = -40 V I_{D} = -13 A$

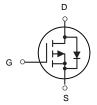
 $R_{DS(ON)}$ < 19m Ω @ V_{GS} =10V

Application

Battery protection

Load switch

Uninterruptible power supply



P-Channel MOSFET

Package Marking and Ordering Information

Product ID	Pack	Brand	Qty(PCS)
STP9527	SOP-8	HXY MOSFET	3000

Absolute Maximum Ratings (Tc=25°C unless otherwise noted)

Symbol	Parameter	Rating	Units
V _{DS}	Drain-Source Voltage	- 40	V
VGS	Gate-Source Voltage	±20	V
I _D @T _A =25°C	Drain Current ³ , V _{GS} @ 10V	-13	А
IDM	Pulsed Drain Current ¹	-52	А
P _D @T _A =25°C	Total Power Dissipation	3	W
TSTG	Storage Temperature Range	-55 to 150	°C
TJ	Operating Junction Temperature Range	-55 to 150	°C
Rthj-a	Maximum Thermal Resistance, Junction-ambient ³	41	°C/W



Electrical Characteristics (T_J = 25°C, unless otherwise noted)

Parameter		Symbol	Test Conditions	Min.	Тур.	Max.	Unit	
Static Characteristics								
Drain-Source Breakdown Voltage		V _{(BR)DSS}	V _{GS} = 0V, I _D = -250μA -4		-	-	V	
Gate-body Leakage current		Igss	V _{DS} = 0V, V _{GS} = ±20V -		-	±100	nA	
Zero Gate Voltage Drain Current	TJ=25°C	IDSS	V _{DS} = -40V, V _{GS} = 0V	-	-	-1	μА	
	T _J =100°C			-	-	-100		
Gate-Threshold Voltage	1	V _{GS(th)}	V _{DS} = V _{GS} , I _D = -250μA -1.		-1.5	-2.2	V	
		_	V _{GS} = -10V, I _D = -10A	-	14.0	19		
Drain-Source On-Resistance ⁴		R _{DS(on)}	V _{GS} = -4.5V, I _D = -5 A	-	19.5	25	mΩ	
Forward Transconductance ⁴		g fs	V _{DS} = -10V, I _D = -10A	-	44	-	S	
Dynamic Characteristics5	i				l	I.		
Input Capacitance		C _{iss}		-	2525	-		
Output Capacitance		Coss	V _{DS} = -20V, V _{GS} =0V, f =1MHz	-	190	-	pF	
Reverse Transfer Capacitance		C _{rss}		-	172	-		
Gate Resistance		Rg	f=1MHz	-	10	-	Ω	
Switching Characteristics	5	l		l		ı		
Total Gate Charge		Qg		-	35	-		
Gate-Source Charge		Qgs	$V_{GS} = -10V, V_{DS} = -20V,$ $I_{D} = -10A$	-	5.5	-	nC	
Gate-Drain Charge		Q _{gd}		-	8	-		
Turn-On Delay Time		t _{d(on)}		-	14.5	-	. ns	
Rise Time		tr	$V_{GS} = -10V, V_{DD} = -20V,$	-	20.2	-		
Turn-Off Delay Time		t _{d(off)}	$R_G = 3\Omega$, $I_D = -10A$	-	32	-		
Fall Time		tf		-	10	-		
Drain-Source Body Diode	Character	istics	1			1		
Diode Forward Voltage ⁴		V _{SD}	I _S = -10A, V _{GS} = 0V	-	_	-1.2	V	
Continuous Source Current	T _C =25°C	ls	-	-	-	-13	Α	

Note:

- 1. Repetitive rating, pulse width limited by junction temperature $T_{J(MAX)}$ =150°C.
- 2. The EAS data shows Max. rating . The test condition is V_{DD} = -25V, V_{GS} = -10V, L= 0.1mH, I_{AS} = -34A.
- 3. The data tested by surface mounted on a 1 inch2 FR-4 board with 2OZ copper, The value in any given application depends on the user's specific board design.
- 4. The data tested by pulsed , pulse width \leq 300us , duty cycle \leq 2%.
- $5.\ \mbox{This}$ value is guaranteed by design hence it is not included in the production test.



Typical Characteristics

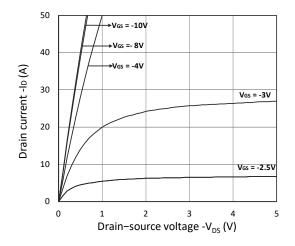


Figure 1. Output Characteristics

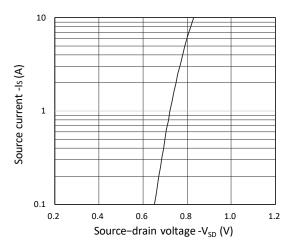


Figure 3. Forward Characteristics of Reverse

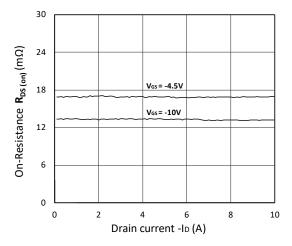


Figure 5. $R_{DS(ON)}$ vs. I_D

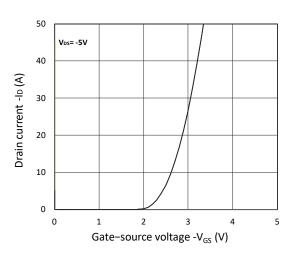


Figure 2. Transfer Characteristics

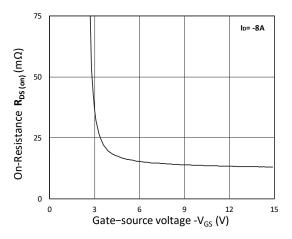


Figure 4. $R_{DS(ON)}$ vs. V_{GS}

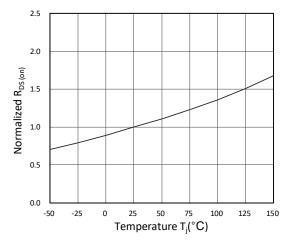


Figure 6. Normalized $R_{DS(on)}$ vs. Temperature

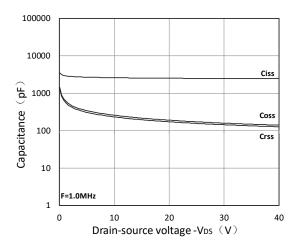


Figure 7. Capacitance Characteristics

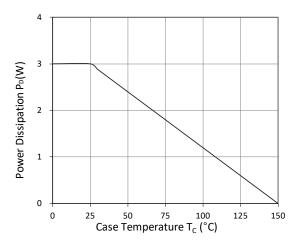


Figure 9. Power Dissipation

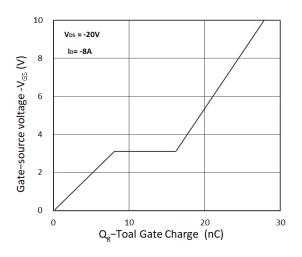


Figure 8. Gate Charge Characteristics

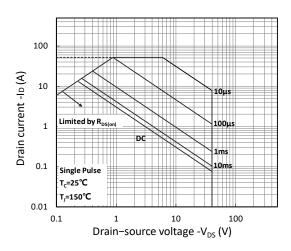


Figure 10. Safe Operating Area

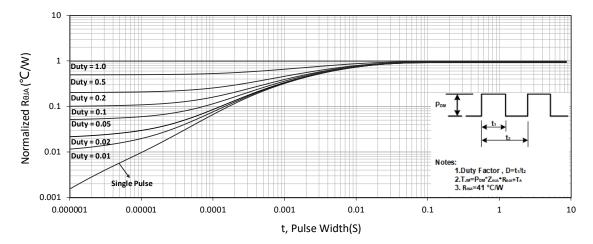


Figure 11. Normalized Maximum Transient Thermal Impedance



Test Circuit

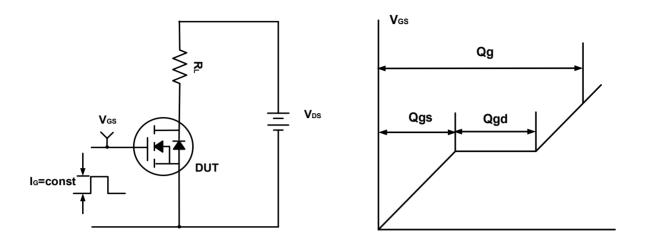


Figure A. Gate Charge Test Circuit & Waveforms

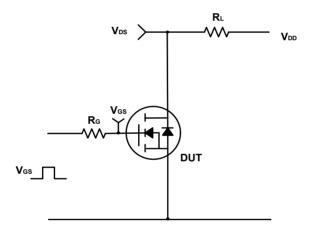


Figure B. Switching Test Circuit & Waveforms

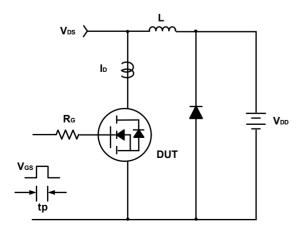
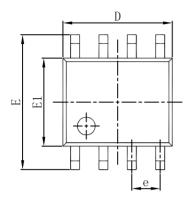
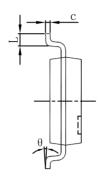


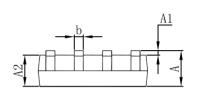
Figure C. Unclamped Inductive Switching Circuit & Waveforms



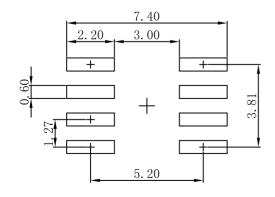
SOP-8 Package Outline Dimensions







Symbol	Dimensions In Millimeters		Dimensions In Inches		
	Min	Max	Min	Max	
A	1. 350	1.750	0.053	0.069	
A1	0.100	0. 250	0.004	0.010	
A2	1.350	1.550	0.053	0.061	
b	0.330	0.510	0.013	0.020	
c	0.170	0.250	0.007	0.010	
D	4.800	5.000	0.189	0. 197	
e	1.270 (BSC)		0.050 (BSC)		
E	5.800	6. 200	0. 228	0. 244	
E1	3.800	4.000	0.150	0. 157	
L	0.400	1. 270	0.016	0.050	
θ	0°	8°	0°	8°	



- Note: 1.Controlling dimension:in millimeters.
- 2.General tolerance:± 0.05mm.
 3.The pad layout is for reference purposes only.



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